



# IEEE SW Test Workshop

Semiconductor Wafer Test Workshop

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# New Generation of Probe Alloys

Dr. Edward F Smith, III, Jason Kumnick, Bruce Quimby, Art Klein Deringer-Ney, Inc.



## SME

## **Overview**

Increases in overall wafer size coupled with ever decreasing feature size places tremendous pressure on optimizing the materials used for semiconductor test probes.

This is especially true as the test environment pushes to smaller diameter probes required by today's micro and nano revolution.

It is well known that material characteristics such as electrical conductivity and hardness play a key role in probe performance.

However, other material properties (temper, formability, etc.) may also influence performance, reliability and life cycle cost of the probes.





## **Presentation Outline**

- Semiconductor History
  - Impact of more powerful IC's
  - Product evolution demanding smaller probes
- Relevant Material Properties
  - Spring Constant
  - Hardness
  - Conductivity CCC Performance
  - Formability
- Important Factors Affecting Lifetime
  - Starting temper & Forming
  - Prolonged thermal exposure





# **Quick Review of IC History**





## **IC Evolution**

- Overall wafer size getting larger
  - More dies per wafer
  - More complex testing protocol
- Feature size getting smaller
  - Maintain function smaller components
  - Increased function more power, higher test currents
  - Higher test temperatures





## **Power Consequences**

- Transistor count increases with Moore's law
   Doubles approximately every 2 years
- Higher transistor count means more power
- More power means test probes must carry more current
- More current means probes run hotter





# **Test Probes**





## **Evolution of Vertical Probe Size**

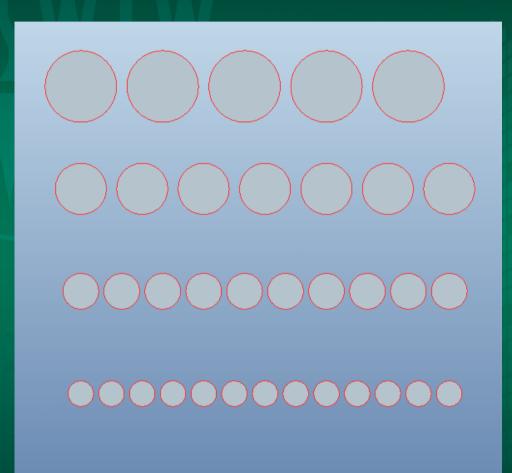
1978 – 0.178 mm (.007")

1985 – 0.127 mm (.005")

2000 – 0.089 mm (.0035")

2009 – 0.064 mm (.0025")

2013 – 0.038 mm (.0015")



.......





# Single Probe in Card

FORCE (Touchdown)

Single Probe

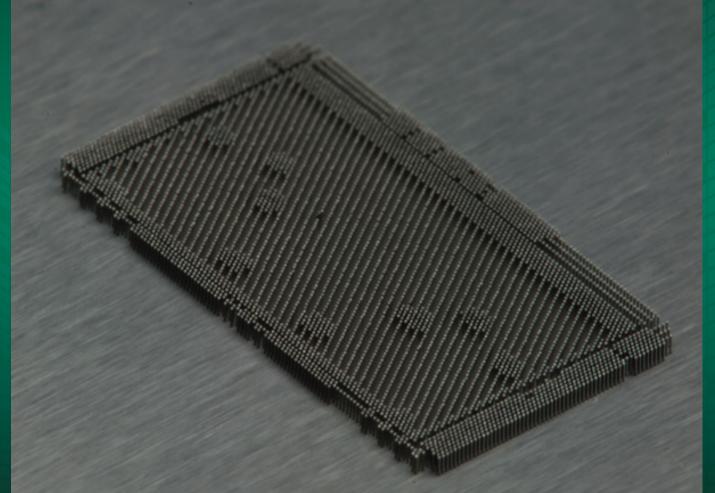


Center Buckles
And applies force

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# **Fully Populated Card**



Array can approach 10,000 pins





## **Size Consequences**

- Chip Real Estate is at a premium
- Higher density of smaller features
- Result- pad sizes must shrink
- Since probe tips must contact the pads
- Probe diameter/ tips must also get smaller
- Smaller diameter means probes run hotter





# **Noble Metal Alloy Options**





# **Alloy Properties**

(Nominal)

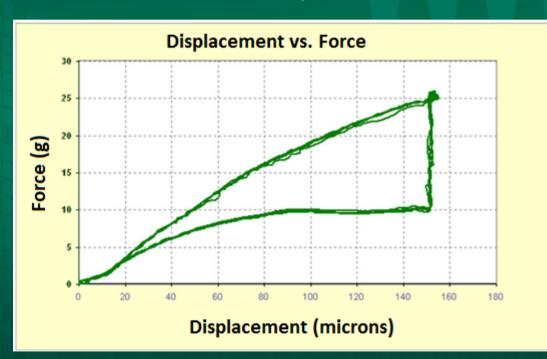
Properties	Paliney 7 (Pd-Ag-Cu-Pt-Au)	Paliney H3C (Pd-Ag-Cu)	Paliney C (Pd-Ag-Cu)
HT Conductivity (%IACS)	5.5	14.5	16.5
Annealed UTS Hardness	120 ksi 230Hv	170 ksi 260Hv	125 ksi 260Hv
Heat Treated UTS Hardness	180 ksi 380Hv	250 ksi 475Hv	190 ksi 385Hv
Benefits	High nobility, Low C <sub>R</sub>	High Conductivity High Hardness, Low C <sub>R</sub>	High Conductivity, Low C <sub>R</sub>

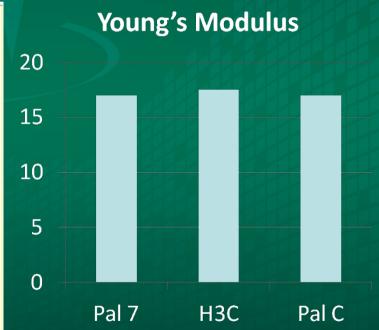




## **Material Properties**

- Spring Constant Affects Gram Force
  - Controlled by Elastic Modulus and Geometry



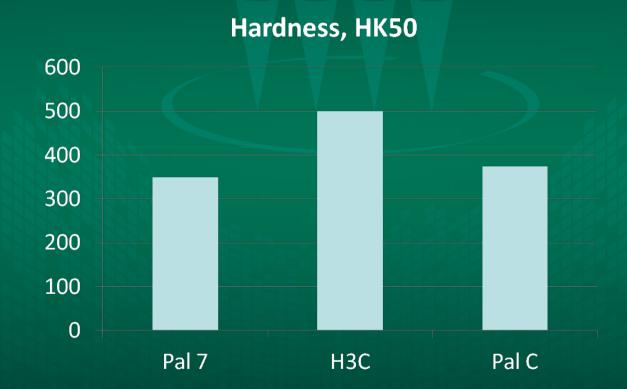






## **Material Properties**

Hardness – Affects wear / point life





# Material properties -Formability

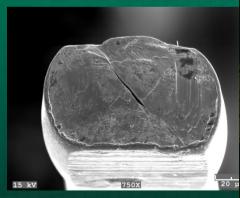
SME

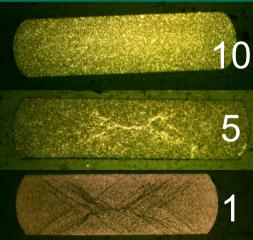
#### Measurement Techniques

- Repeated 90° bends
  - # of Bends
  - Modified protocol
    - Improved reproducibility



- Roll to Ribbon
  - Rated on a scale 1-10
  - 1 =Open Cracks
  - 10 = No Visible Strain Lines



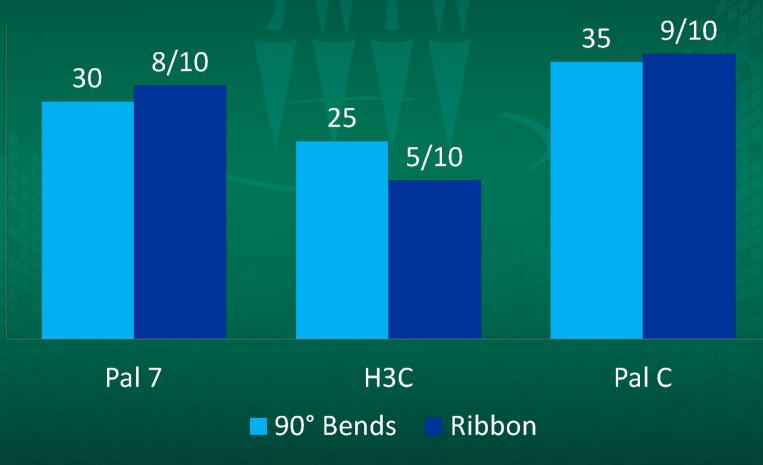




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# **Results of Formability Tests**



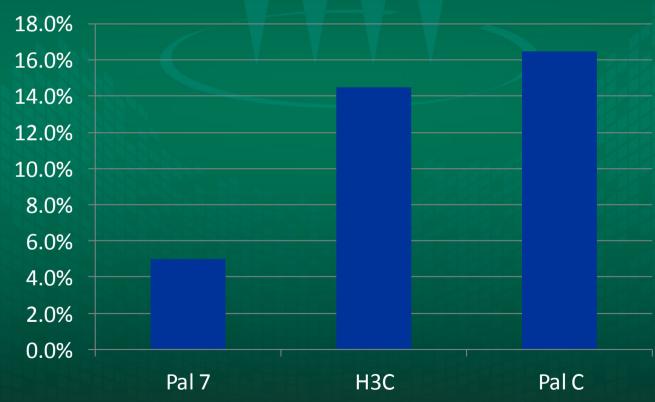




# **Material Properties**

• Electrical Conductivity %IACS

#### Conductivity





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## **CCC** Testing

### **Current Carrying Capacity (CCC)**

#### Methodology

Load probe to recommended overdrive

Measure gram force

Apply current to the probe – to reach steady state

**Turn current off** 

Allow the probe to cool

Measure gram force of Probe at the end of each current cycle

**Incrementally increase current** 

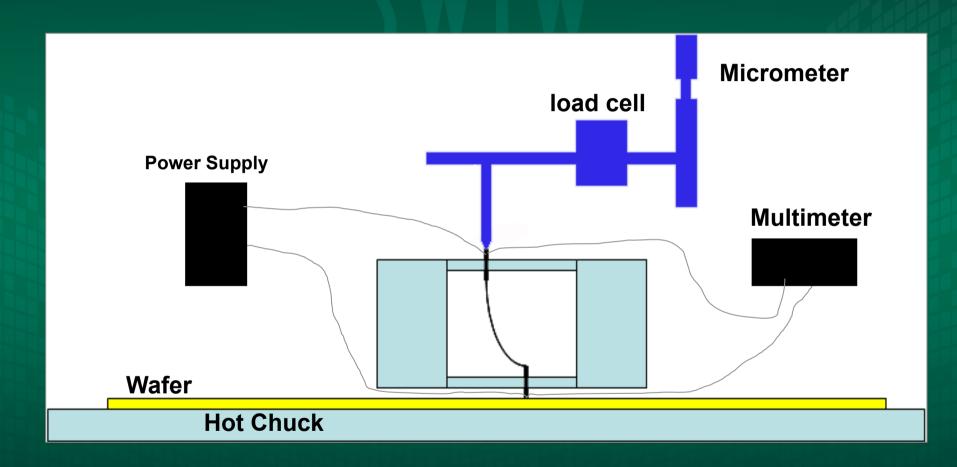
Repeat process until gram force is less than 80% of initial gram force

<u>CCC defined as the current level where probe force</u> <u>is 20% lower than the initial force</u>





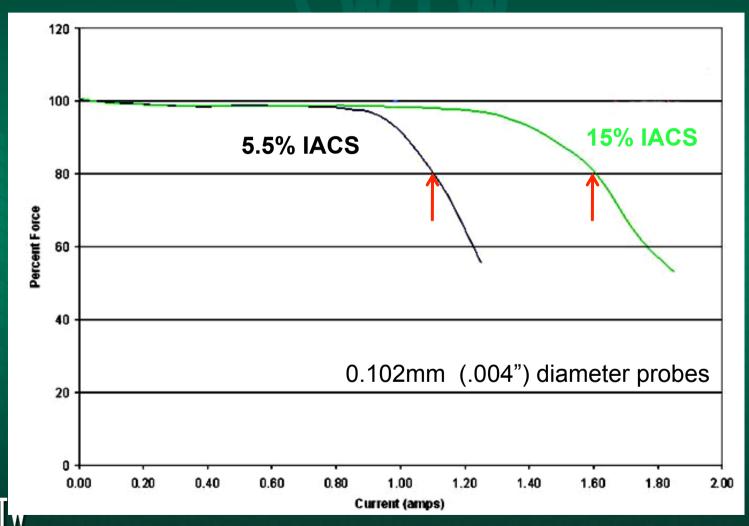
## **CCC** test cell







# **Effect of Electrical Conductivity**





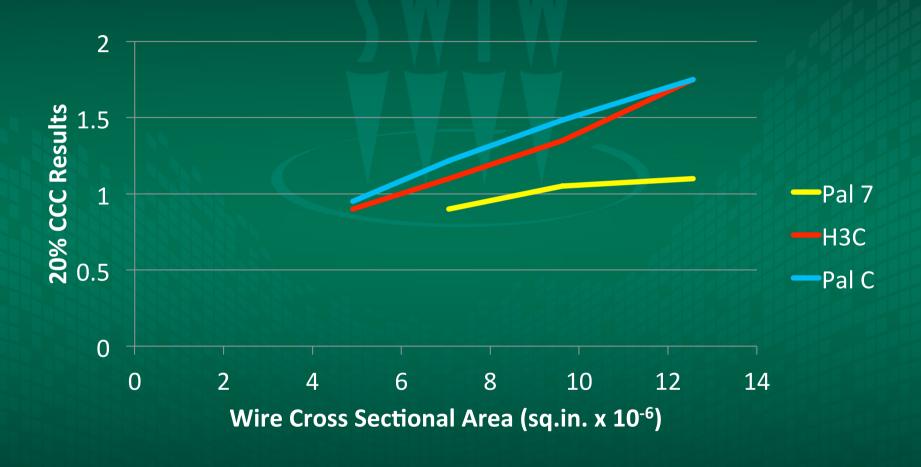
# **Alloy CCC Data**

100	Paliney 7	Paliney H3C	Paliney C
<b>Probe Size</b>	(5.5% IACS)	(14.5% IACS)	(16.5% IACS)
4.0 mil	1.10 A	1.75A	1.75A
3.5 mil	1.05A	1.35A	
3.0 mil	.90A	1.10A	
2.5 mil		0.95A	0.95A





# **Alloy CCC Data**









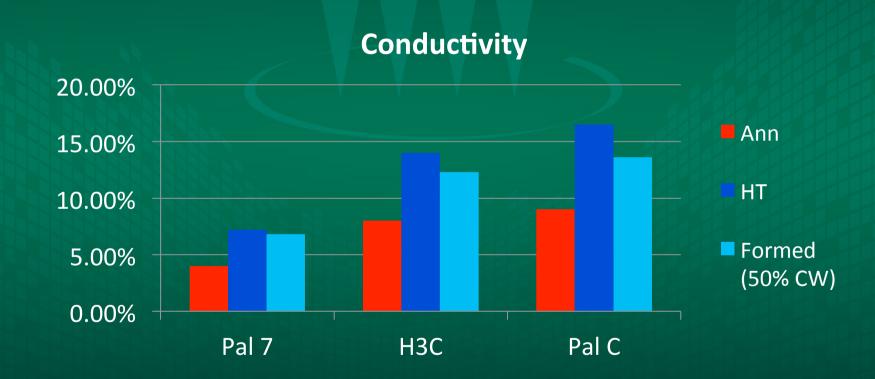
- Initial Material Properties are altered by:
  - Probe Forming
  - Prolonged Thermal Exposure
- Re-evaluate properties in process





# **Factors Affecting Probe Lifetime**

Starting temper and Affect of cold work (forming)

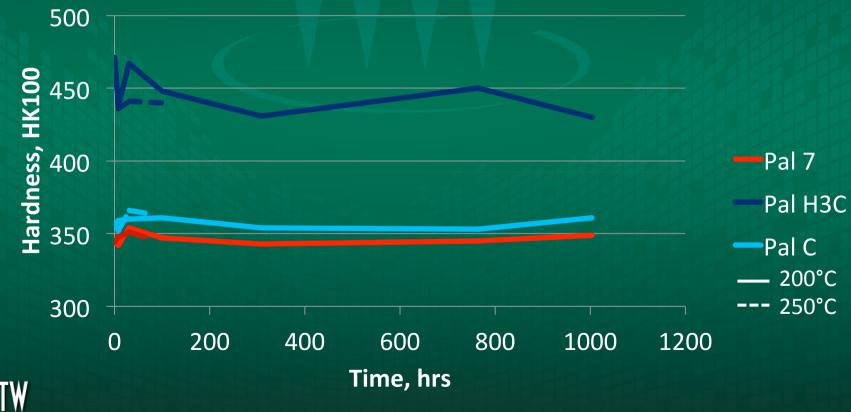






# **Factors Affecting Probe Lifetime**

- Prolonged thermal exposure
  - Alloy Softening 200°C



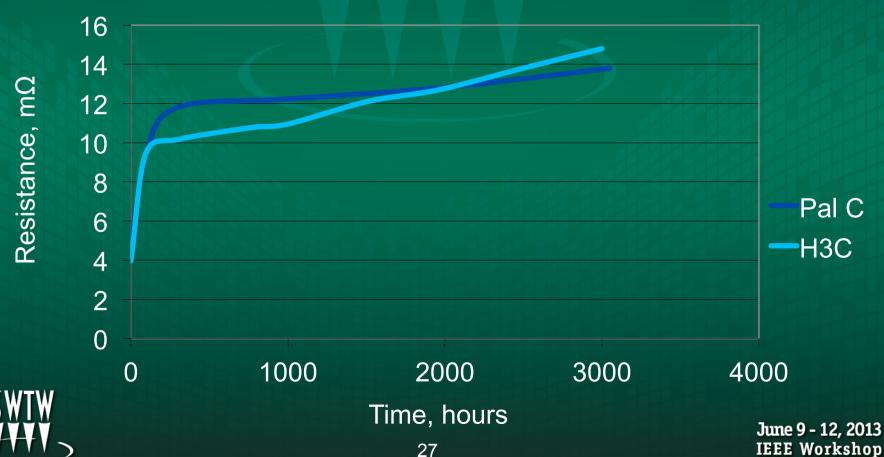




# **Factors Affecting Probe Lifetime**

Prolonged thermal exposure

Contact Resistance 125°C Air Oxidation





## **Conclusions**

- Current Market demands optimized materials
  - Electrical Conductivity and Hardness play key role in determining material performance.
- Reliability and life cycle cost also determined by:
  - Starting Temper
  - Testing Environment
  - Probe Forming





## **Conclusions**

#### Notable DNI Materials for Probes

- Paliney 7
  - Industry Benchmark Low Conductivity
- Paliney H3C
  - High Hardness and Conductivity, Lower Formability
- Paliney C
  - Hardness of Paliney 7
  - Higher conductivity than H3C.
  - Increased Formability





## Acknowledgements

The authors would like thank Joey Wu of MPI for performing and sharing the ccc tests and the spring rate measurements

We would also like to thank Scott Marquis and Dave Birdsall from our lab for all their assistance during the development and testing of these new alloys





# Questions?





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## Thank you!

Dr. Edward F. Smith, III

Deringer Ney, Inc.

